Lecture 10

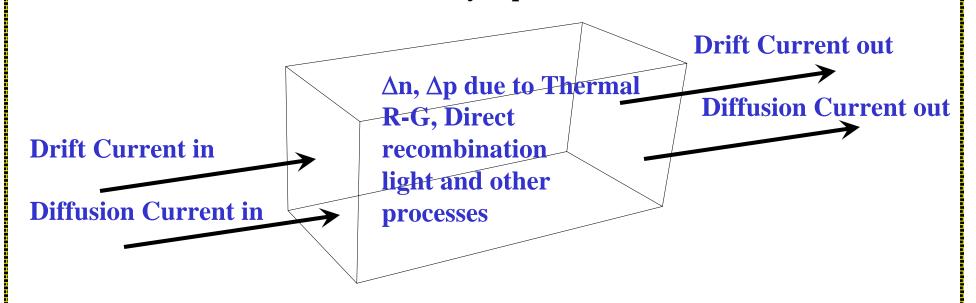
Equations of State, Minority Carrier Diffusion Equation and Quasi-Fermi Levels

Reading:

(Cont'd) Notes and Anderson² sections 3.4-3.11 and chapter 4

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Ways carrier concentrations can be altered Continuity Equations



$$\frac{\partial n}{\partial t} = \frac{\partial n}{\partial t} \Big|_{Drift} + \frac{\partial n}{\partial t} \Big|_{Diffusion} + \frac{\partial n}{\partial t} \Big|_{Re\ combination-Generation} + \frac{\partial n}{\partial t} \Big|_{All\ other\ processes\ such\ as\ light,\ etc...}$$

$$\frac{\partial p}{\partial t} = \frac{\partial p}{\partial t}\Big|_{Drift} + \frac{\partial p}{\partial t}\Big|_{Diffusion} + \frac{\partial p}{\partial t}\Big|_{Re\ combination-Generation} + \frac{\partial p}{\partial t}\Big|_{All\ other\ processes\ such\ as\ light,\ etc...}$$

There must be spatial and time continuity in the carrier concentrations

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Ways carrier concentrations can be altered Continuity Equations

$$\frac{\partial n}{\partial t}\Big|_{Drift} + \frac{\partial n}{\partial t}\Big|_{Diffusion} = \frac{1}{q} \left(\frac{\partial J_{Nx}}{\partial x} + \frac{\partial J_{Ny}}{\partial y} + \frac{\partial J_{Nz}}{\partial z} \right) = \frac{1}{q} \nabla \cdot J_{N}$$

$$\frac{\partial p}{\partial t}\Big|_{Drift} + \frac{\partial p}{\partial t}\Big|_{Diffusion} = -\frac{1}{q} \left(\frac{\partial J_{Px}}{\partial x} + \frac{\partial J_{Py}}{\partial y} + \frac{\partial J_{Pz}}{\partial z} \right) = -\frac{1}{q} \nabla \cdot J_{P}$$

Divergence in the current

$$\frac{\partial n}{\partial t} = \frac{1}{q} \nabla \cdot J_N + \frac{\partial n}{\partial t} \Big|_{\text{Re combination-Generation}} + \frac{\partial n}{\partial t} \Big|_{\substack{\text{All other processes such as light, etc...}}}$$

$$\frac{\partial p}{\partial t} = -\frac{1}{q} \nabla \cdot \boldsymbol{J}_{P} + \frac{\partial p}{\partial t} \Big|_{\text{Re combination-Generation}} + \frac{\partial p}{\partial t} \Big|_{\substack{\text{All other processes such as light, etc...}}}$$

Continuity Equations: Special Case known as "Minority Carrier Diffusion Equation"

Simplifying Assumptions:

- 1) One dimensional case. We will use "x".
- 2) We will only consider minority carriers

Continuity Equation

Minority Carrier Diffusion Equation

- 3) Electric field is approximately zero in regions subject to analysis.
- 4) The minority carrier concentrations IN EQUILIBRIUM are not a function of position.
- 5) Low-level injection conditions apply.
- 6) SRH recombination-generation is the main recombination-generation mechanism.
- 7) The only "other" mechanism is photogeneration.

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Continuity Equations: Special Case known as "Minority Carrier Diffusion Equation"

Because of (3) - no electric field ...

Since
$$E = 0$$
, ...

$$J_{n} = J_{n} |_{Drift} + J_{n} |_{Diffusion} = q \mu_{n} n E + q D_{n} \nabla n$$

$$J_n = J_n \mid_{Diffusion} = qD_n \frac{\partial n}{\partial x}$$

$$\frac{1}{q}\nabla \cdot \boldsymbol{J}_{N} = \frac{1}{q}\frac{\partial \boldsymbol{J}_{N}}{\partial x} = D_{n}\frac{\partial^{2} \boldsymbol{n}}{\partial x^{2}} = D_{n}\frac{\partial^{2} (\boldsymbol{n}_{o} + \Delta \boldsymbol{n})}{\partial x^{2}} = D_{n}\frac{\partial^{2} (\Delta \boldsymbol{n})}{\partial x^{2}}$$

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Continuity Equations: Special Case known as "Minority Carrier Diffusion Equation"

Because of (5) - low level injection ...

$$\frac{\partial n}{\partial t}\Big|_{\text{Re combination-Generation}} = -\frac{\Delta n}{\tau_n}$$

Because of (7) - no other process ...

$$\left. \frac{\partial n}{\partial t} \right|_{\substack{All \ other \ processes \ such \ as \ light, \ etc...}} = G_L$$

Continuity Equations: Special Case known as "Minority Carrier" **Diffusion Equation**"

Finally ...

$$\frac{\partial n}{\partial t} = \frac{\partial (n_o + \Delta n)}{\partial t} = \frac{\partial (\Delta n)}{\partial t}$$

$$\frac{\partial n}{\partial t} = \frac{\partial n}{\partial t} \Big|_{Drift} + \frac{\partial n}{\partial t} \Big|_{Diffusion} + \frac{\partial n}{\partial t} \Big|_{Re\ combination-Generation} + \frac{\partial n}{\partial t} \Big|_{All\ other\ processes\ such\ as\ light,\ etc...}$$

$$\frac{\partial (\Delta n_p)}{\partial t} = D_N \frac{\partial^2 (\Delta n_p)}{\partial x^2} - \frac{(\Delta n_p)}{\tau_n} + G_L$$

$$Or$$

$$Or$$

$$Minority$$
Carrier
Diffusion

$$\frac{\partial(\Delta p_n)}{\partial t} = D_P \frac{\partial^2(\Delta p_n)}{\partial x^2} - \frac{(\Delta p_n)}{\tau_p} + G_L$$

Carrier **Diffusion Equations**

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Continuity Equations: Special Case known as "Minority Carrier Diffusion Equation" - Further simplifications

Steady State ...

$$\frac{\partial (\Delta n_p)}{\partial t} \to 0 \quad and \quad \frac{\partial (\Delta p_n)}{\partial t} \to 0$$

No minority carrier diffusion gradient ...

$$D_N \frac{\partial^2 (\Delta n_p)}{\partial x^2} \to 0 \quad and \quad D_P \frac{\partial^2 (\Delta p_n)}{\partial x^2} \to 0$$

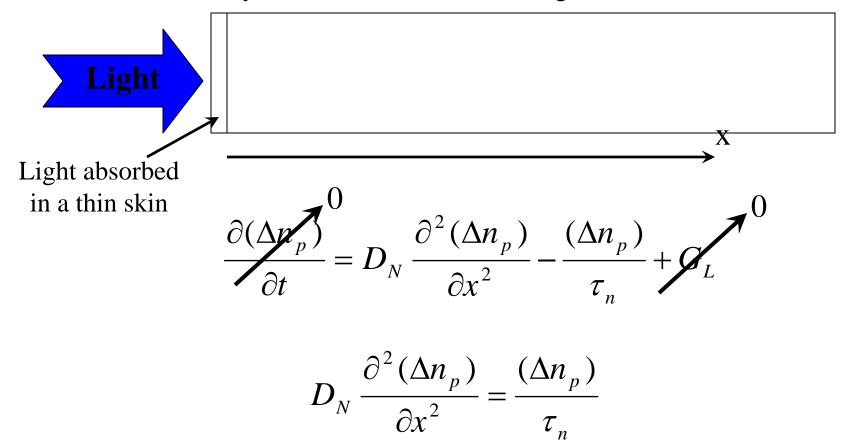
No SRH recombination-generation ...

$$\frac{\Delta n_p}{\tau_n} = 0 \quad and \quad \frac{\Delta p_n}{\tau_p} = 0$$

No Light ...

$$G_L \to 0$$

Consider a semi-infinite p-type silicon sample with $N_A=10^{15}$ cm⁻³ constantly illuminated by light absorbed in a very thin region of the material creating a steady state excess of 10^{13} cm⁻³ minority carriers. What is the minority carrier distribution in the region x>0?



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General Solution ...

$$\Delta n_p(x) = Ae^{(-x/L_N)} + Be^{(+x/L_N)}$$
 where $L_N \equiv \sqrt{D_n \tau_n}$

 L_N is the "diffusion length" the average distance a minority carrier can move before recombining with a majority carrier.

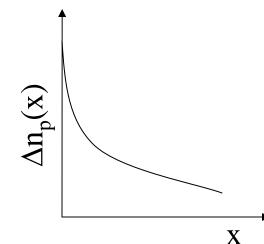
Boundary Condition ...

$$\Delta n_p(x=0) = 10^{13} cm^{-3} = A + B$$

$$\Delta n_p(x = \infty) = 0 = A(0) + Be^{(+\infty/L_N)}$$

$$\Rightarrow B = 0$$

$$\Delta n_p(x) = 10^{13} e^{(-x/L_N)} cm^{-3}$$



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Consider a p-type silicon sample with $N_A=10^{15}$ cm⁻³ and minority carrier lifetime $\tau=1$ uS constantly illuminated by light absorbed uniformly throughout the material creating an excess 10^{13} cm⁻³ minority carriers <u>per second</u>. The light has been on for a very long time. At time t=0, the light is shut off. What is the minority carrier distribution in for t<0?

Light absorbed uniformly

$$\frac{\partial (\Delta n_p)^0}{\partial t} = D_N \frac{\partial^2 (\Delta n_p)}{\partial x^2} - \frac{(\Delta n_p)}{\tau_n} + G_L$$

$$\Delta n_p(all \ x, t < 0) = G_L \tau_n = 10^7 \ cm^{-3}$$

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X

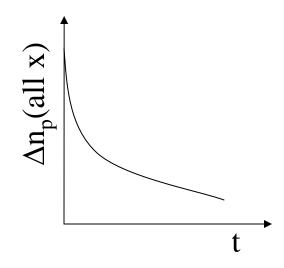
In the previous example: What is the minority carrier distribution in for t>0?



$$\frac{\partial(\Delta n_p)}{\partial t} = D_N \frac{\partial^2(\Delta n_p)}{\partial x^2} - \frac{(\Delta n_p)}{\tau_n} + \mathcal{O}_L$$

$$\Delta n_p(t) = \left[\Delta n_p(t=0)\right] e^{\left(-\frac{t}{\tau_n}\right)}$$

$$\Delta n_p(t) = 10^7 e^{\left(-\frac{t}{1e-6}\right)}$$



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Quasi - Fermi Levels

Equilibrium:
$$n_o = n_i e^{\binom{\left(E_f - E_i\right)}{kT}} \quad and \quad p_o = n_i e^{\binom{\left(E_i - E_f\right)}{kT}}$$

Non-equilibrium:
$$(F_N - E_i)/kT$$
 and $p = n_i e^{(E_i - F_P)/kT}$

N-type Low level injection	N-type High level injection
$\mathbf{E_c}$	$\mathbf{E_c}$
$\mathbf{E_f}, \mathbf{F_N}$	$oxed{\mathbf{E_f^N}}$
$\mathbf{E_i}$	$\mathbf{E_i}$
$\cdots \qquad \mathbf{F_{P}}$	$\mathbf{F}_{\mathbf{p}}$
$\mathbf{E_v}$	$\mathbf{E_v}$
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Quasi - Fermi Levels

$$p = n_{i}e^{\left(\frac{(E_{i} - F_{p})}{kT}\right)}$$

$$\nabla p = \frac{n_{i}}{kT}e^{\left(\frac{(E_{i} - F_{p})}{kT}\right)}\left(\nabla E_{i} - \nabla F_{p}\right)$$

$$\nabla p = \left(\frac{qp}{kT}\right)E - \left(\frac{p}{kT}\right)\nabla F_{p}$$

$$J_{p} = q\mu_{p}pE - qD_{p}\nabla p$$

$$J_{p} = q\left(\mu_{p} - \frac{qD_{p}}{kT}\right)pE + \left(\frac{qD_{p}}{kT}\right)p\nabla F_{p}$$

$$but... \quad \mu_{p} = \frac{qD_{p}}{kT} \quad leading \ to...$$

$$J_{p} = \mu_{p}p\nabla F_{p} \quad and \ similarly \quad J_{N} = \mu_{p}n\nabla F_{N}$$

If there is a change in quasi-fermi levels, current flows!